

## United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO		
10/709,953	06/09/2004	Min-Lung Huang	10546-US-PA	3952		
31561 75	590 09/22/2005		EXAM	EXAMINER		
JIANQ CHYUN INTELLECTUAL PROPERTY OFFICE			WILLIAMS, AI	WILLIAMS, ALEXANDER O		
7 FLOOR-1, NO. 100 ROOSEVELT ROAD, SECTION 2			ART UNIT	PAPER NUMBER		
TAIPEI, 100		2826				
TAIWAN			DATE MAILED: 09/22/2005	5		

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application	No.	Applicant(s)			
		10/709,953		HUANG ET AL.			
	Office Action Summary	Examiner		Art Unit			
		Alexander O.	Williams	2826			
Period f	The MAILING DATE of this communior Reply	nication appears on the co	over sheet with the	correspondence ac	Idress		
WHI - Exte afte - If N - Fail Any	HORTENED STATUTORY PERIOD F CHEVER IS LONGER, FROM THE N ensions of time may be available under the provisions or SIX (6) MONTHS from the mailing date of this come O period for reply is specified above, the maximum stature to reply within the set or extended period for reply reply received by the Office later than three months ned patent term adjustment. See 37 CFR 1.704(b).	MAILING DATE OF THIS s of 37 CFR 1.136(a). In no event, munication. tatutory period will apply and will exy will, by statute, cause the applicat	COMMUNICATION however, may a reply be to spire SIX (6) MONTHS from to become ABANDON	DN. timely filed m the mailing date of this c NED (35 U.S.C. § 133).			
Status							
1)⊠	Responsive to communication(s) file	ed on <i>29 July 2005</i>					
•	This action is <b>FINAL</b> .		-final.				
	Since this application is in condition	•—		rosecution as to the	e merits is		
<i>ن</i> ب	closed in accordance with the pract	·	·				
Disposit	tion of Claims						
4) 🛛	Claim(s) 1-20 is/are pending in the	application.					
,—	4a) Of the above claim(s) <u>4-7 and 13-15</u> is/are withdrawn from consideration.						
5)	Claim(s) is/are allowed.						
	6)⊠ Claim(s) <u>1-3,8-12 and 16-20</u> is/are rejected.						
	Claim(s) is/are objected to.	,					
	Claim(s) are subject to restrict	ction and/or election requ	Jirement.				
Applicat	tion Papers						
9)	The specification is objected to by th	ie Examiner.					
· <u> </u>	The drawing(s) filed-on is/are		objected to by the	: Examiner.			
- /	Applicant may not request that any obje						
	Replacement drawing sheet(s) including		•	, ,	FR 1.121(d)		
11)	The oath or declaration is objected to	·	<b>-</b>	•			
·	under 35 U.S.C. § 119						
_	Acknowledgment is made of a claim	for foreign priority under	35 U.S.C. & 140/	a)-(d) or (f)			
	)⊠ All b)□ Some * c)□ None of:	to totalight priority under	00 0.0.0. 3 113(6	4) (U) OI (I).			
u,	1.⊠ Certified copies of the priority	documents have been r	eceived				
	2. Certified copies of the priority			tion No			
	3. Copies of the certified copies		• •		Stage		
	application from the Internation	•		rod iii uiio Naliullal	Jiage		
* (	See the attached detailed Office action	·	` ' ' '	red.			
Attachmer							
	ce of References Cited (PTO-892) ce of Draftsperson's Patent Drawing Review (F	4) PTO-948)	Interview Summar Paper No(s)/Mail [				
3) 🔲 Infor	mation Disclosure Statement(s) (PTO-1449 or er No(s)/Mail Date	· · · · · · · · · · · · · · · · · · ·		Patent Application (PTC	)-152)		

U.S. Patent and Trademark Office PTOL-326 (Rev. 7-05)

Serial Number: 10/709953 Attorney's Docket #: 10546-US-PA

Filing Date: 6/9/2004; claimed foreign priority to 6/9/2003

Applicant: Huang et al.

**Examiner: Alexander Williams** 

Applicant's election of the species of figure 2 (claims 1 to 3, 8 to 12 and 16 to 20), filed 7/29/05, has been acknowledged.

This application contains claims 4 to 7 and 13 to 15 drawn to an invention nonelected without traverse.

Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed.

The lengthy specification has not been checked to the extent necessary to determine the presence of all possible minor errors. Applicant's cooperation is requested in correcting any errors of which applicant may become aware in the specification.

The following is a quotation of the appropriate paragraphs of 35 U.S.C. § 102 that form the basis for the rejections under this section made in this Office action: A person shall be entitled to a patent unless --

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains.

Patentability shall not be negatived by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(f) or (g) prior art under 35 U.S.C. 103(a).

Claims 1 and 2 are rejected under 35 U.S.C. § 102(e) as being anticipated by Hashimoto (U.S. Patent # 6,583,516 B2).

1. Hashimoto (figures 1 to 17) specifically figure 10c show a chip structure, comprising: a chip having a first passivation layer 108 and at least a bonding pad 104, wherein the bonding pad is exposed by the first passivation layer and the first passivation layer has at least a recess; a redistribution layer 110 formed over the first passivation layer, wherein the redistribution layer electrically connects with the bonding pad and extends from the bonding pad to the recess; a second passivation layer 116 formed over the first passivation layer and the redistribution layer, wherein the second passivation layer has

an opening **108a** that exposes the redistribution layer above the recess; and at least a bump **114** disposed inside the opening and electrically connected to the redistribution layer above the recess.

- 2. The chip structure of claim I, Hashimoto show wherein an obtuse angle is formed between a sidewall of the recess and a bottom surface; of the recess.
- 3. The chip structure of claim 1, Hashimoto further comprising at least an under-bump-metallurgy layer **112** between the redistribution layer that is exposed by the opening and the bump.

Claims 1 and 2 are rejected under 35 U.S.C. § 102(e) as being anticipated by Huang (U.S. Patent # 6,452,270 B1).

- 1. Huang (figures 1 to 8) specifically figure 8 show a chip structure 400, comprising: a chip having a first passivation layer 330 and at least a bonding pad 320, wherein the bonding pad is exposed by the first passivation layer and the first passivation layer has at least a recess; a redistribution layer 440 formed over the first passivation layer, wherein the redistribution layer electrically connects with the bonding pad and extends from the bonding pad to the recess; a second passivation layer 450 formed over the first passivation layer and the redistribution layer, wherein the second passivation layer has an opening 450a that exposes the redistribution layer above the recess; and at least a bump 470 disposed inside the opening and electrically connected to the redistribution layer above the recess.
- 2. The chip structure of claim I, Huang show wherein an obtuse angle is formed between a sidewall of the recess and a bottom surface; of the recess.

Claims 1 to 3 are rejected under 35 U.S.C. § 102(e) as being anticipated by Horng (U.S. Patent Application Publication # 2004/0266163 A1).

1. Horng (figures 1 to 11) specifically figure 11 show a chip structure 200, comprising: a chip having a first passivation layer 205 and at least a bonding pad 202, wherein the bonding pad is exposed by the first passivation layer and the first passivation layer has at least a recess; a redistribution layer 208,211 formed over the first passivation layer,

Art Unit: 2826

wherein the redistribution layer electrically connects with the bonding pad and extends from the bonding pad to the recess; a second passivation layer 212 formed over the first passivation layer and the redistribution layer, wherein the second passivation layer has an opening that exposes the redistribution layer above the recess; and at least a bump 213 disposed inside the opening and electrically connected to the redistribution layer above the recess.

- 2. The chip structure of claim I, Horng show wherein an obtuse angle is formed between a sidewall of the recess and a bottom surface; of the recess.
- 3. The chip structure of claim 1, Horng further comprising at least an under-bump-metallurgy layer **208,211** between the redistribution layer that is exposed by the opening and the bump.

Applicant cannot rely upon the foreign priority papers to overcome this rejection because a translation of said papers has not been made of record in accordance with 37 CFR 1.55. See MPEP § 201.15.

Initially, it is noted that the 35 U.S.C. § 103 rejection based on a first metallic layer formed over the opening-exposed redistribution layer; a second metallic layer formed over the first metallic layer; and a third metallic layer formed over the second metallic layer deals with an issue (i.e., the integration of multiple pieces into one piece or conversely, using multiple pieces in replacing a single piece) that has been previously decided by the courts.

In <u>Howard v. Detroit Stove Works</u> 150 U.S. 164 (1893), the Court held, "it involves no invention to cast in one piece an article which has formerly been cast in two pieces and put together...."

In <u>In re Larson</u> 144 USPQ 347 (CCPA 1965), the term "integral" did not define over a multi-piece structure secured as a single unit. More importantly, the court went further and stated, "we are inclined to agree with the solicitor that the

Art Unit: 2826

use of a one-piece construction instead of the [multi-piece] structure disclosed in Tuttle et al. would be merely a matter of obvious engineering choice" (bracketed material added). The court cited In re Fridolph for support.

In re Fridolph 135 USPQ 319 (CCPA 1962) deals with submitted affidavits relating to this issue. The underlying issue in In re Fridolph was related to the end result of making a multi-piece structure into a one-piece structure. Generally, favorable patentable weight was accorded if the one-piece structure yielded results not expected from the modification of the two-piece structure into a single piece structure.

Claims 8, 9, 11, 12, 16, 17, 19 and 20 are rejected under 35 U.S.C. § 103(a) as being unpatentable over Huang (U.S. Patent # 6,452,270 B1).

- 8. The chip structure of claim 3, Huang et al. show wherein the under bump-metallurgy layer further comprises; a first metallic layer **440a** formed over the opening-exposed redistribution layer; a second metallic layer **440b,440c** formed over the first metallic layer; and a third metallic layer **440b,440c** formed over the second metallic layer.
- 9. The chip structure of claim 8, Huang et al. show wherein a material constituting the first metallic layer is selected from the group consisting of aluminum, **titanium**, titanium-tungsten alloy, tantalum, tantalum nitride and chromium.
- 11. The chip structure of claim 8, Huang et al. show wherein a material constituting the third metallic layer comprises copper **440b**.
- 12. The chip structure of claim 8, Huang et al. show wherein the under-bump-metallurgy layer further comprises at least an electroplated layer **460b** formed over the third metallic layer and the electroplated layer is selected from the group consisting of **an electroplated copper layer**, an electroplated nickel layer, an electroplated gold layer and combination thereof.
- 16. The chip structure of claim 1, Huang et al. show wherein the redistribution layer further comprises: a first metallic layer **440a** formed over the first passivation layer; a

second metallic layer 440b,440c formed over the first metallic layer, and a third metallic layer 440b,440c formed over the second metallic layer.

- 17. The chip structure of claim 16, Huang et al. show wherein a material constituting the first metallic layer is selected from the group consisting of alumimun, **titanium**, titanium-tungsten alloy, tantalum, tantalum nitride and chromium.
- 19. The chip structure of claim 16, Huang et al. show wherein a material constituting the third metallic layer comprise: copper.
- 20. The chip structure of claim 1, Huang et al. show wherein an obtuse angle **450a** is formed between a sidewall of the opening and a bottom surface of the opening.

Therefore, it would have been obvious to one of ordinary skill in the art to use the first metallic layer formed over the opening-exposed redistribution layer; a second metallic layer formed over the first metallic layer; and a third metallic layer formed over the second metallic layer as "merely a matter of obvious engineering choice" as set forth in the above case law.

Initially, it is noted that the 35 U.S.C. § 103 rejection based on a first metallic layer formed over the opening-exposed redistribution layer; a second metallic layer formed over the first metallic layer; and a third metallic layer formed over the second metallic layer and an under-bump-metallurgy layer and the redistribution layer deals with an issue (i.e., the integration of multiple pieces into one piece or conversely, using multiple pieces in replacing a single piece) that has been previously decided by the courts.

Claims 3, 8 to 12 and 16 to 20 are rejected under 35 U.S.C. § 103(a) as being unpatentable over Hashimoto (U.S. Patent # 6,583,516 B2).

3. The chip structure of claim 1, Hashimoto further comprising at least an under-bump-metallurgy layer **112** between the redistribution layer that is exposed by the opening and the bump.

Art Unit: 2826

8. The chip structure of claim 3, Hashimoto show wherein the under bump-metallurgy layer further comprises; a first metallic layer 112 formed over the opening-exposed redistribution layer; a second metallic layer 112 formed over the first metallic layer; and a third metallic layer 112 formed over the second metallic layer (see column 6, lines 55-63).

Page 8

- 9. The chip structure of claim 8, Hashimoto show wherein a material constituting the first metallic layer is selected from the group consisting of aluminum, **titanium, titanium-tungsten alloy**, tantalum, tantalum nitride and chromium (see column 6, lines 55-63).
- 10. The chip structure of claim 8, Hashimoto show wherein a material constituting the second metallic layer is selected from the- group consisting of nickel-vanadium alloy and **copper-chromium alloy**.
- 11. The chip structure of claim 8, Hashimoto show wherein a material constituting the third metallic layer comprises **copper**.
- 12. The chip structure of claim 8, Hashimoto show wherein the under-bump-metallurgy layer further comprises at least an electroplated layer formed over the third metallic layer and the electroplated layer is selected from the group consisting of **an electroplated copper layer**, an electroplated nickel layer, an electroplated gold layer and combination thereof.
- 16. The chip structure of claim 1, Hashimoto show wherein the redistribution layer further comprises: a first metallic layer 112 formed over the first passivation layer; a second metallic layer 112 formed over the first metallic layer, and a third metallic layer 112 formed over the second metallic layer.
- 17. The chip structure of claim 16, Hashimoto show wherein a material constituting the first metallic layer is selected from the group consisting of alumimun, **titanium**, **titanium**, **titanium**, **titanium**,
- 18. The chip structure of claim 16, Hashimoto show wherein a material constituting the second metallic layer is selected from the group consisting of nickel-vanadium alloy and copper-chromium alloy.
- 19. The chip structure of claim 16, Hashimoto show wherein a material constituting the third metallic layer comprise: copper.

20. The chip structure of claim 1, Hashimoto show wherein an obtuse angle is formed between a sidewall of the opening and a bottom surface of the opening.

Therefore, it would have been obvious to one of ordinary skill in the art to use the first metallic layer formed over the opening-exposed redistribution layer; a second metallic layer formed over the first metallic layer; and a third metallic layer formed over the second metallic layer as "merely a matter of obvious engineering choice" as set forth in the above case law.

Claims 3, 8 to 12 and 16 to 20 are rejected under 35 U.S.C. § 103(a) as being unpatentable over Huang (U.S. Patent # 6,452,270 B1).

- 3. The chip structure of claim 1, Horng further comprising at least an under-bump-metallurgy layer **208,211** between the redistribution layer **208,211** that is exposed by the opening and the bump.
- 8. The chip structure of claim 3, Horng show wherein the under bump-metallurgy layer further comprises; a first metallic layer 211,208 formed over the opening-exposed redistribution layer; a second metallic layer 208,211 formed over the first metallic layer; and a third metallic layer 208,211 formed over the second metallic layer (see paragraph [0026]).
- 9. The chip structure of claim 8, Horng show wherein a material constituting the first metallic layer is selected from the group consisting of aluminum, **titanium**, titanium-tungsten alloy, tantalum, tantalum nitride and chromium.
- 10. The chip structure of claim 8, Horng show wherein a material constituting the second metallic layer is selected from the- group consisting of nickel-vanadium alloy and copper-chromium alloy.
- 11. The chip structure of claim 8, Horng show wherein a material constituting the third metallic layer comprises copper.
- 12. The chip structure of claim 8, Horng show wherein the under-bump-metallurgy layer further comprises at least an electroplated layer 208,211 formed over the third metallic layer and the electroplated layer is selected from the group consisting of **an**

electroplated copper layer, an electroplated nickel layer, an electroplated gold layer and combination thereof.

- 16. The chip structure of claim 1, Horng show wherein the redistribution layer further comprises: a first metallic layer 208,211 formed over the first passivation layer; a second metallic layer 208,211 formed over the first metallic layer, and a third metallic layer 208,211 formed over the second metallic layer.
- 17. The chip structure of claim 16, Horng show wherein a material constituting the first metallic layer is selected from the group consisting of alumimun, **titanium**, titanium-tungsten alloy, tantalum, tantalum nitride and chromium.
- 18. The chip structure of claim 16, Horng show wherein a material constituting the second metallic layer is selected from the group consisting of nickel-vanadium alloy and copper-chromium alloy.
- 19. The chip structure of claim 16, Horng show wherein a material constituting the third metallic layer comprise: copper.
- 20. The chip structure of claim 1, Horng show wherein an obtuse angle is formed between a sidewall of the opening and a bottom surface of the opening.

Therefore, it would have been obvious to one of ordinary skill in the art to use the first metallic layer formed over the opening-exposed redistribution layer; a second metallic layer formed over the first metallic layer; and a third metallic layer formed over the second metallic layer as "merely a matter of obvious engineering choice" as set forth in the above case law.

Applicant cannot rely upon the foreign priority papers to overcome this rejection because a translation of said papers has not been made of record in accordance with 37 CFR 1.55. See MPEP § 201.15.

The listed references are cited as of interest to this application, but not applied at this time.

Art Unit: 2826

Field of Search	Date
U.S. Class and subclass: 257/737,734,738,700,701,758,781,782,783,773,774,772,7 79,780,761,763,764,765,766	9/15/05
Other Documentation: foreign patents and literature in 257/737,734,738,700,701,758,781,782,783,773,774,772,7 79,780,761,763,764,765,766	9/15/05
Electronic data base(s): U.S. Patents EAST	9/15/05

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Alexander O. Williams whose telephone number is (571) 272 1924. The examiner can normally be reached on M-F 6:30AM-7:00PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (571) 272 1915. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Alexander O Williams
Primary Examiner
Art Unit 2826

AOW 9/19/05